TOSHIBA Transistor Silicon NPN Triple Diffused Type

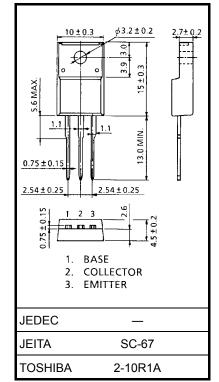
2SD2204

High-Power Switching Applications Hammer Drive, Pulse Motor Drive Applications

- High DC current gain: $h_{FE} = 2000 \text{ (min)} (V_{CE} = 3 \text{ V}, I_{C} = 1.5 \text{ A})$
- Low saturation voltage: V_{CE} (sat) = 1.5 V (max) (I_C = 1.5 A)

Absolute Maximum Ratings (Tc = 25°C)

Characteristics S		ymbol	Rating	Unit	
Collector-base voltage		V _{CBO}	65 ± 10	V	
Collector-emitter voltage		V _{CEO}	65 ± 10	V	
Emitter-base voltage		V _{EBO}	7	V	
Collector current	DC I	С	4	А	
	Pulse I	CP	6	~	
Base current		Ι _Β	0.5	А	
Collector power dissipation	Ta = 25°C	Pc	2.0	W	
	Tc = 25°C	ГC	25	vv	
Junction temperature		T _j 150		°C	
Storage temperature range		T _{stg}	-55 to 150	°C	



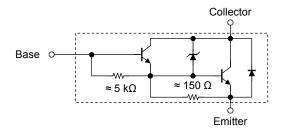
Weight: 1.7 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high

temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Equivalent Circuit

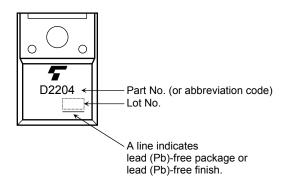


Unit: mm

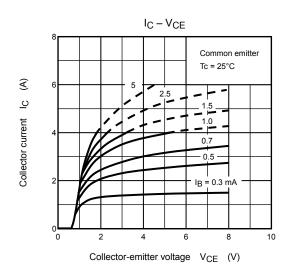
Electrical Characteristics (Tc = 25°C)

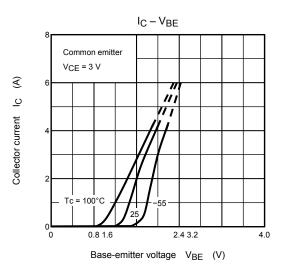
Chara	acteristics S	ymbol	Test Condition	Min	Тур.	Max	Unit	
Collector cut-off c	current	I _{CBO}	V _{CB} = 45 V, I _E = 0	_	— 10	0	μA	
Emitter cut-off current		I _{EBO}	V _{EB} = 6 V, I _C = 0	_	<u> </u>	5	mA	
Collector-emitter breakdown voltage		V (BR) CEO	I _C = 10 mA, I _B = 0	55 65 75			V	
DC current gain		h _{FE (1)}	V _{CE} = 3 V, I _C = 1.5 A	2000	—	15000		
		h _{FE (2)}	V _{CE} = 3 V, I _C = 3 A	1000	—	_		
Collector-emitter saturation voltage		V _{CE (sat) (1)}	I _C = 1.5 A, I _B = 3 mA	—	—	1.5	v	
		V _{CE (sat) (2)}	I _C = 3 A, I _B = 12 mA	—	—	2.0	v	
Base-emitter saturation voltage		V _{BE (sat)}	I _C = 1.5 A, I _B = 3 mA	—	— 2.0	9	V	
	Turn-on time	t _{on}	$Input B_1 \\ 0 utput \\ B_2 \\ V_{CC} \approx 30 V$ $I_{B1} = -I_{B2} = 3 \text{ mA, duty cycle} \le 1\%$	— 1.0)	_	μs	
	Storage time	t _{stg}		— 5.0)	_		
	Fall time	t _f		— 2.0		_		

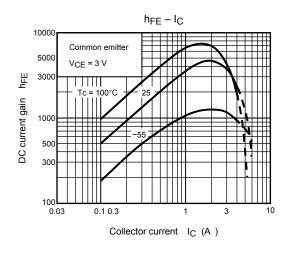
Marking

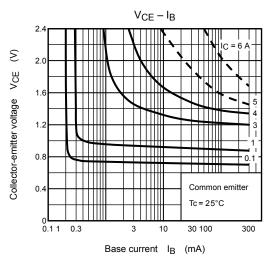


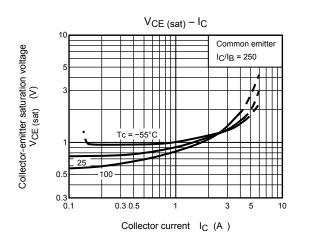
TOSHIBA

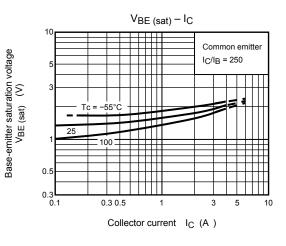


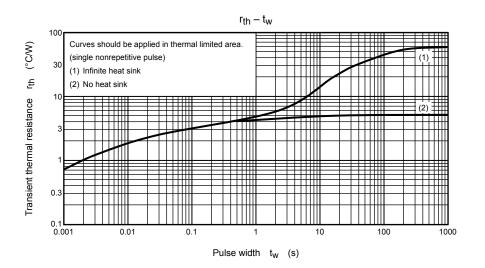




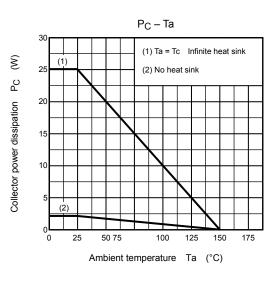








Safe Operating Area 10 100 µs* IC max (pulse)* 10 ms* IC max (continu 1 ms € Collector current IC DC operation Tc = 25°C 0.5 *: Single nonrepetitive pulse 0.3 Tc=25°C Curves must be derated linearly with increase in temperature. VCEO max 0.1 35 10 30 50 100 Collector-emitter voltage V_{CE} (V)



RESTRICTIONS ON PRODUCT USE

20070701-EN

- The information contained herein is subject to change without notice.
- TOSHIBA is continually working to improve the quality and reliability of its products. Nevertheless, semiconductor devices in general can ma lfunction or fail due to their in herent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to comply with the st andards of safety in making a safe design for the entire system, and to avoid situations in which a malfunction or failure of such TOSHIBA products could cause loss of human life, bodily injury or damage to property.
 In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent T OSHIBA product specifications. Also, ple ase keep in m ind the precautions and conditions set forth in the "Handling Guide for Semiconductor Devices," or "TOSHIBA Semiconductor Reliability Handbook" etc.
- The TOSHIBA prod ucts liste d in this document are intended for usage in general electronics a pplications (computer, personal equipment, office equipment, measuring equipment, industrial robotics, domestic appliances, etc.). These T OSHIBA prod ucts are neither intended n or warranted for usage in equipment that requires extraordinarily high quality and/or reliability or a malfunction or failure of which may cause loss of human life or bodily injury ("Unintended Usage"). Unintended Usage in clude atom ic energy control instruments, airplane or spaceship instruments, trans portation instruments, traffic signal instruments, combustion control instruments, medical instruments, all types of safet y devices, et c.. Unintended Usage of T OSHIBA products list ed in his document shall be made at the customer's own risk.
- The products described in this document shall not be used or emb edded to an y downstream products of which manufacture, use and/or sale are prohibited under any applicable laws and regulations.
- The information cont ained h erein is presented only as a guide for the applications of our products. No responsibility is assumed by TOSHIBA for a ny infringements of platents or other rights of the third platties which may result from its use. No license is granted by implication or otherwise under any platents or other rights of TOSHIBA or the third platties.
- Please cont act y our sales repres entative for product- by-product det ails in this document regar ding RoHS compatibility. Please us e these products in this docum ent in compliance with all a pplicable laws and regulations that regulate the incl usion or use of controlled subst ances. Toshiba assumes no liab ility for damage or losse s occurring as a result of noncompliance with applicable laws and regulations.